XED: EXPOSING ON-DIE ERROR DETECTION INFORMATION FOR STRONG MEMORY RELIABILITY

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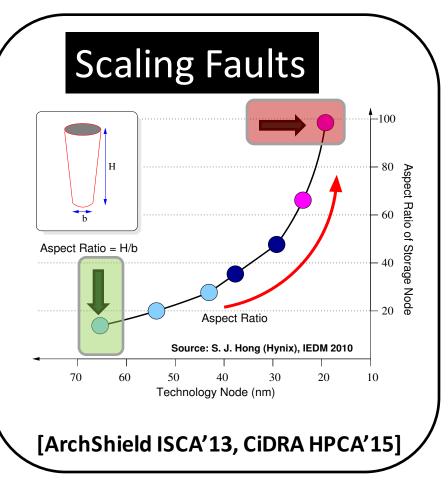
ISCA-43, June 20th 2016 Seoul, Republic of Korea





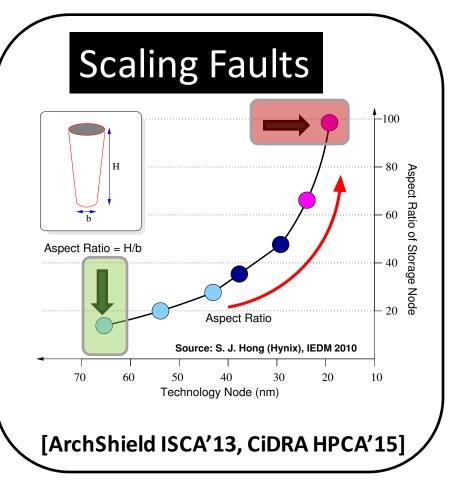
INTRODUCTION

DRAM Scaling → High Capacity Memories Two types of DRAM faults



INTRODUCTION

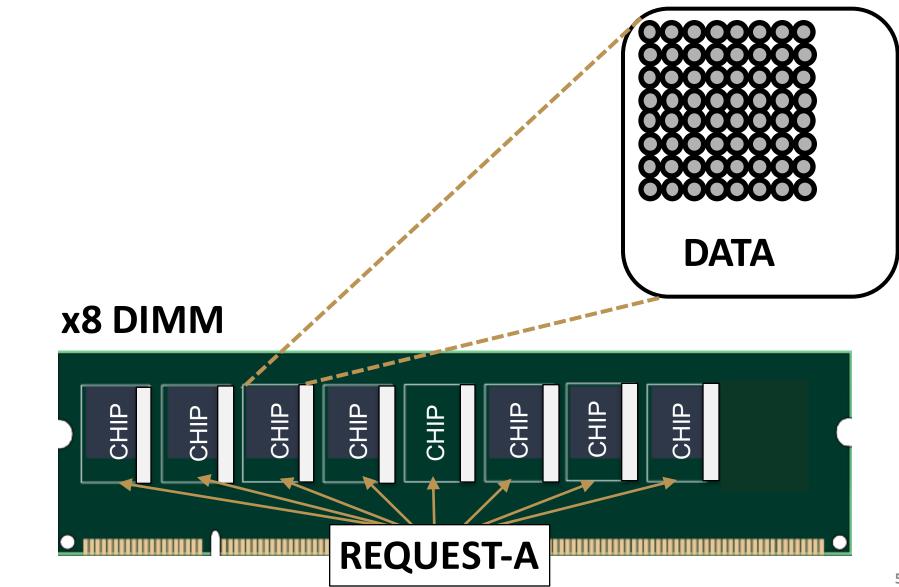
DRAM Scaling → High Capacity Memories Two types of DRAM faults

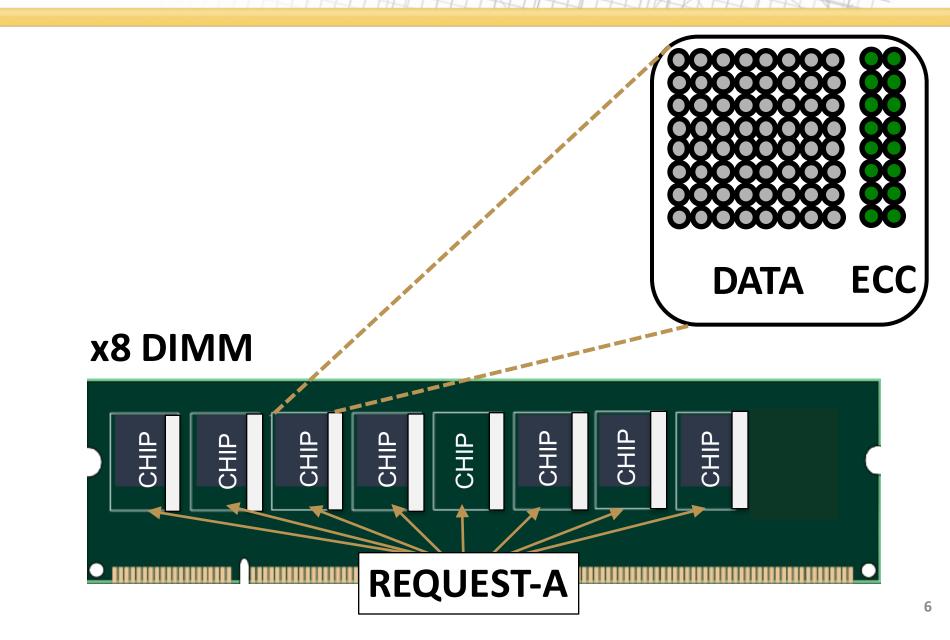


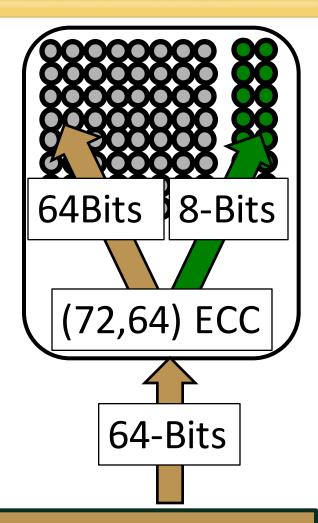
Runtime Faults						
Fault Mode	Transient Fault Rate (FIT)	Permanent Fault Rate (FIT)				
Bit	14.2	18.6				
Word	1.4	0.3				
Column	1.4	5.6				
Row	0.2	8.2				
Bank	0.8	10				
*Total	18	42.7				
Sridharan et. al. SC13						

DRAM vendors plan to use "On-Die ECC"

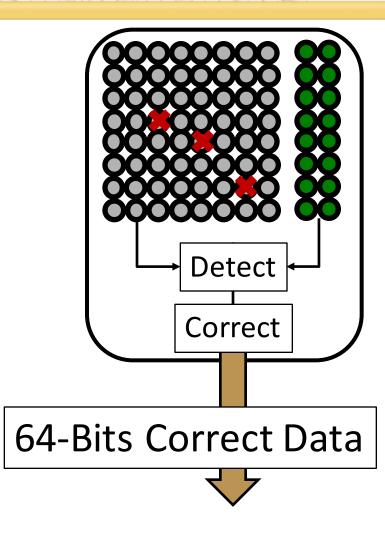
- Mitigates scaling faults transparently
- Enables good DIMM with bad chips (yield)
- Part of: LPDDR4, DDR4, DDR5 (proposed)







On-Die ECC: Single Error Correction, Double Error Detection Code (SECDED)



On-Die ECC fixes scaling faults invisibly

Runtime faults

Fault	Transient	Permanent		
Mode	Fault Rate (FIT)	Fault Rate (FIT)		
Bit	14.2	18.6		

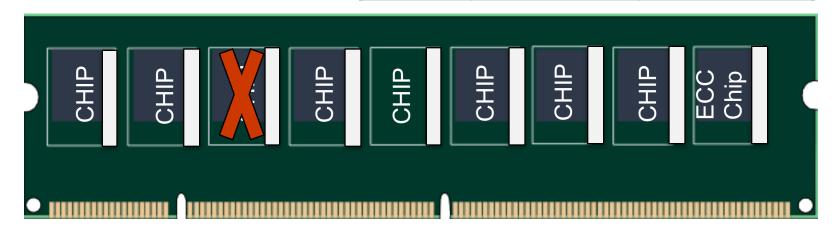
ECC-DIMM (9-Chips)

	CHIP	CHIP	CHIP CHIP	CHIP	CHIP	CHIP	CHIP	CHIP	ECC Chip	

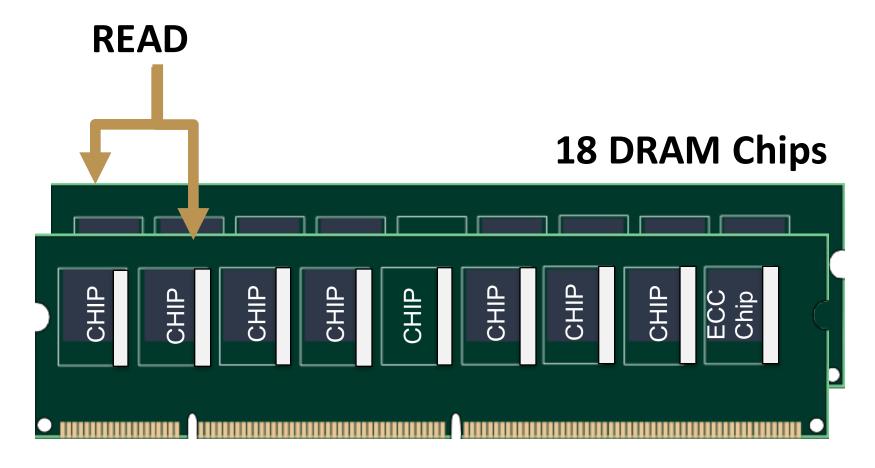
Runtime faults

- Chip faults common
- Need strong ECC

Fault Mode	Transient Fault Rate (FIT)	Permanent Fault Rate (FIT)
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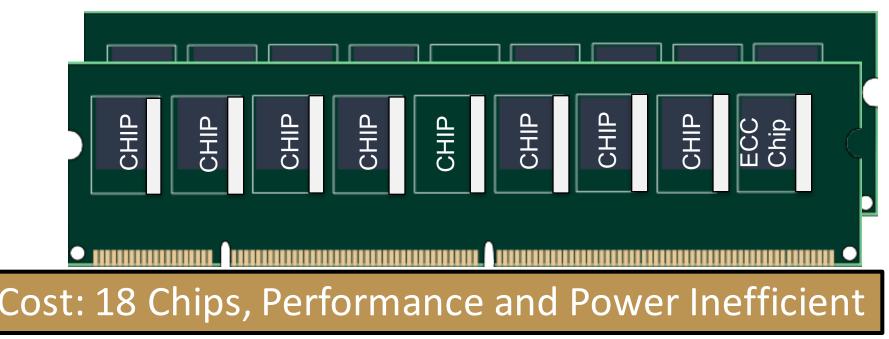


Runtime chip faults \rightarrow Chipkill (strong ECC)



Runtime chip faults \rightarrow Chipkill (strong ECC)

18 DRAM Chips



GOAL AND CHALLENGE

<u>GOAL</u>: Use On-Die ECC to mitigate runtime faults "Chipkill-level reliability using x8 ECC-DIMM"

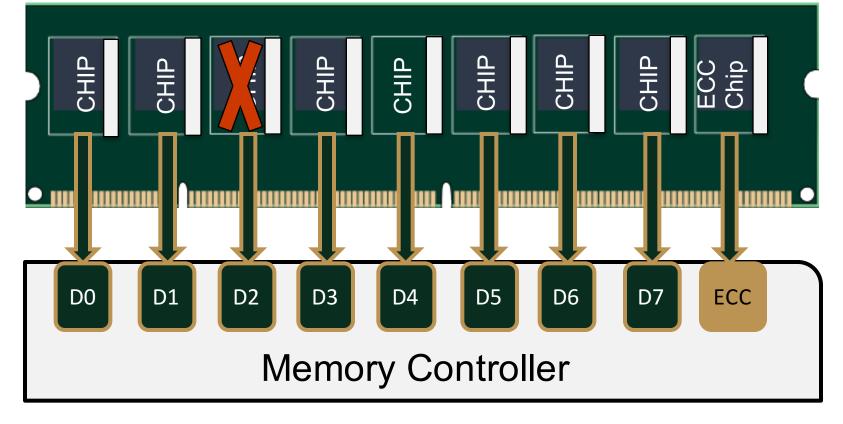
<u>CHALLENGE</u>: On-Die ECC is invisible, expose it without changing the memory interface

OUTLINE

- BACKGROUND
- XED
- CASE STUDIES
- EVALUATION
- SUMMARY

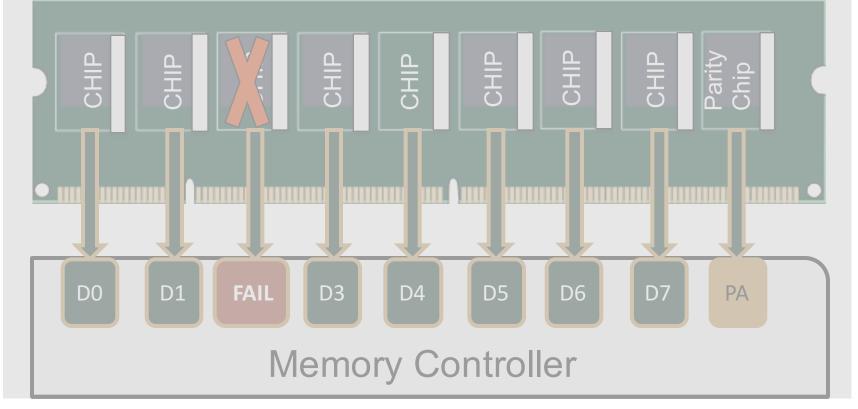
USING PARITY + FAILED LOCATION

What if the chip can inform that it failed?



USING PARITY + FAILED LOCATION

What if the chip can inform that it failed?



Parity + Location \rightarrow Reconstruct Data for Faulty Chip

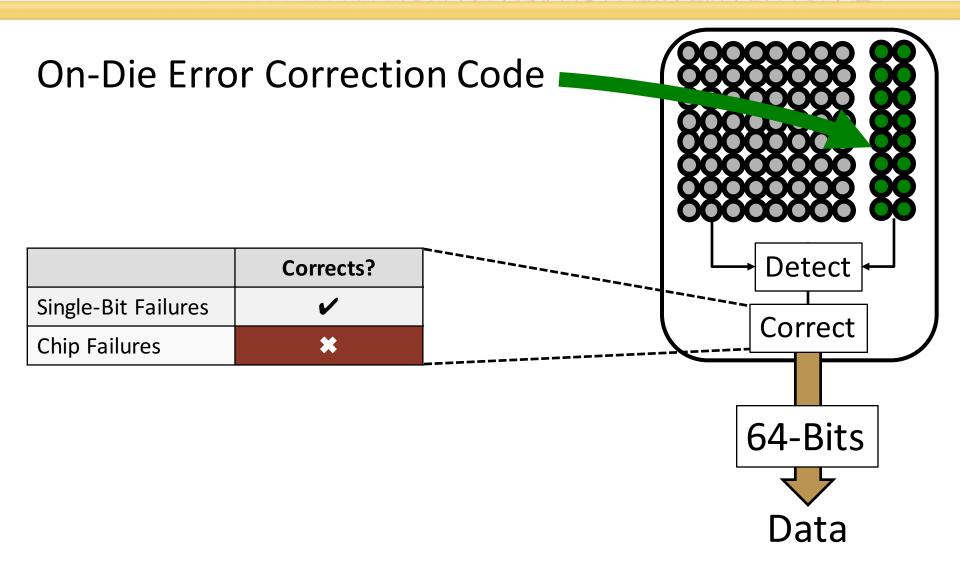
Fix chip-faults using only 9 Chips

XED: EXPOSED ON-DIE ERROR DETECTION

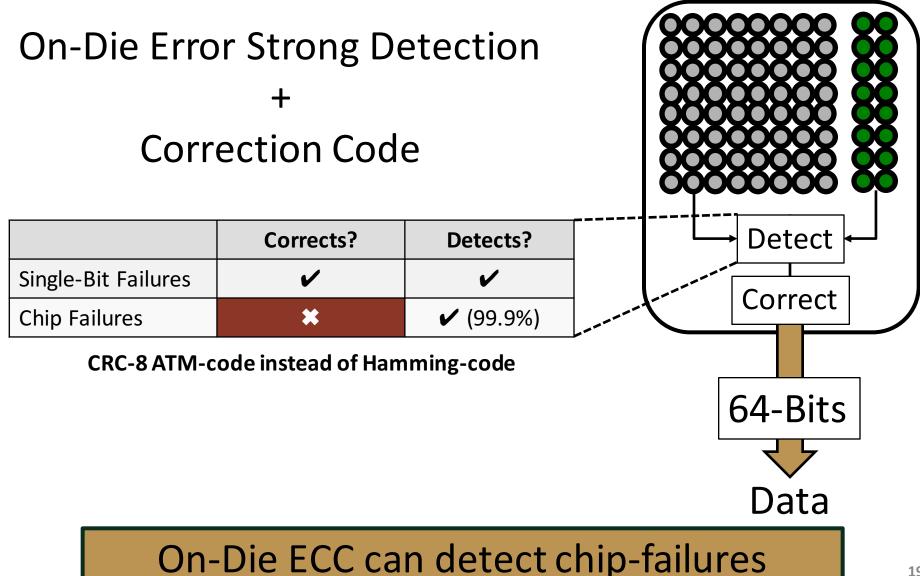
XED consists of three components

- Strong detection in addition to SEC
- Parity-based correction
- Transparently identifying faulty chip

XED: ON-DIE ECC AS DETECTION CODE

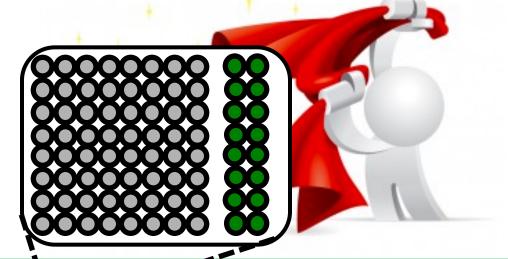


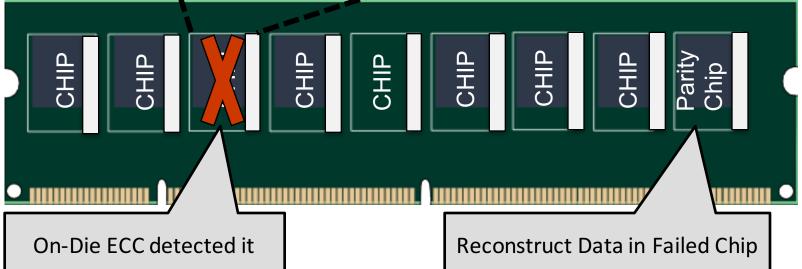




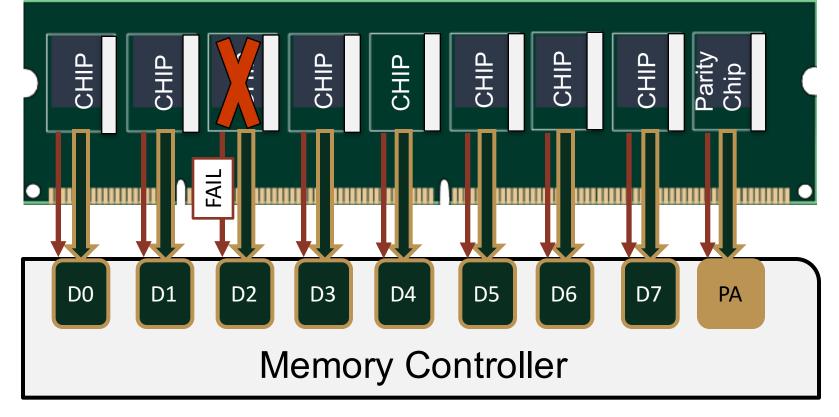
XED: RAID-3 BASED CORRECTION

If we could expose On-Die Error Detection \rightarrow Chipkill





OPTION 1: Use additional wires







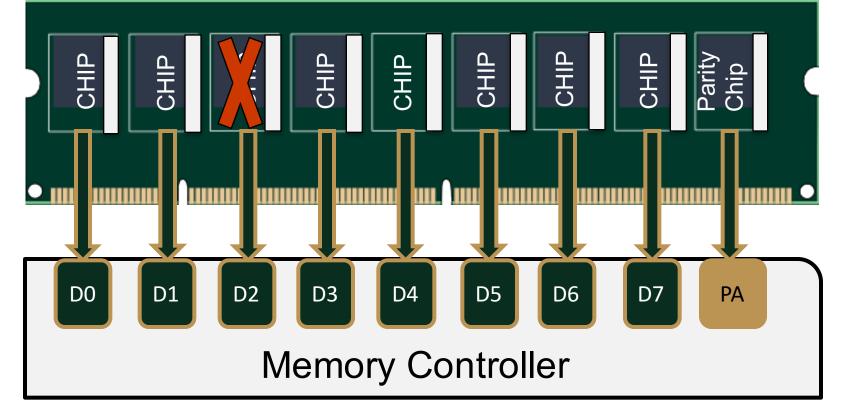
Incompatible with DDR memory standards

Needs a new protocol

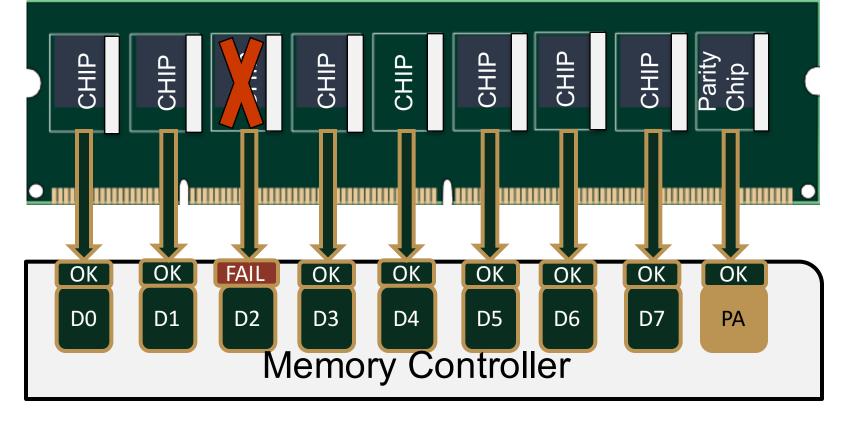
Worse for pin-constrained future systems!

Memory Controller

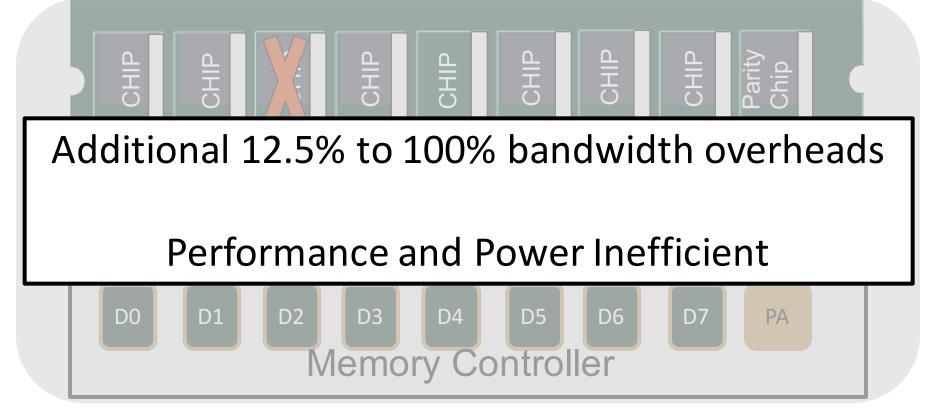
OPTION 2: Use additional burst/transaction



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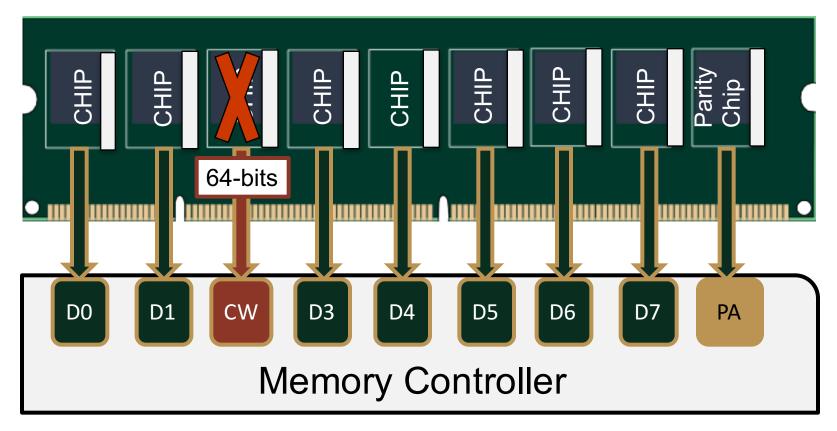
OPTION 2: Use additional burst/transaction



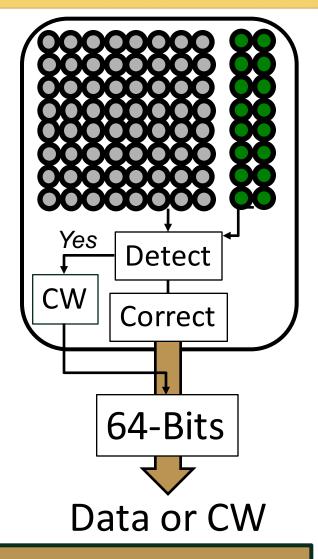
Expose On-Die error detection with minor changes

XED: ON-DIE ERROR INFO FOR FREE

On detecting an error, the DRAM chip sends a 64bit "Catch-Word" (CW) instead of data



XED: MUX TO SEND CATCH-WORDS



Simple MUX to chose between Data and Catch-Word

XED: ON-DIE ERROR INFO FOR FREE

On detecting an error, the DRAM chip sends a 64bit "Catch-Word" (CW) instead of data

Chips provisioned with a unique Catch-Word

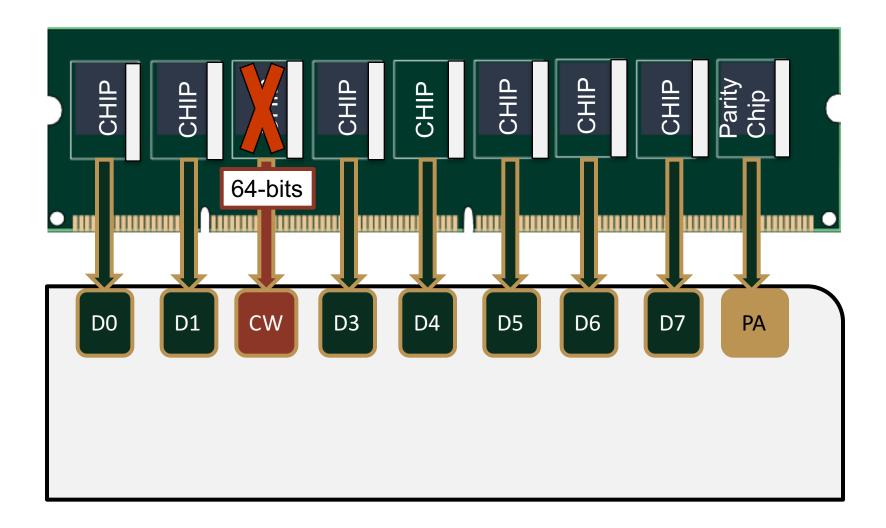
No additional wires/bandwidth overheads

Compatible with existing memory protocols

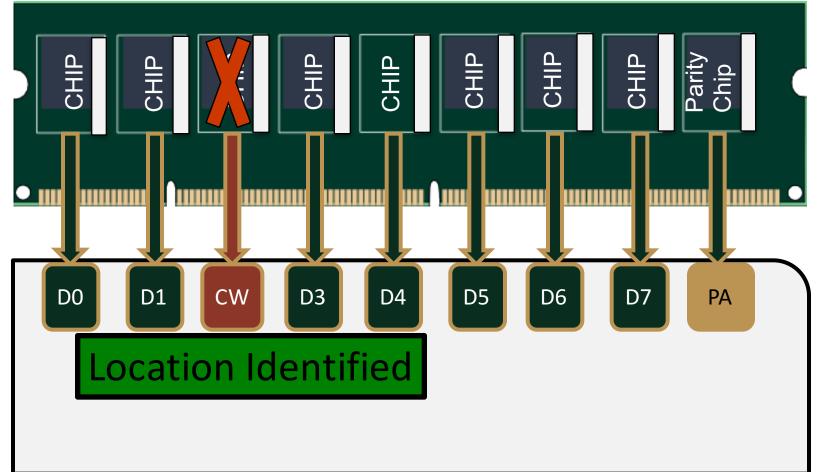
Memory Controller

64-bit Catch-Words identify the faulty chip

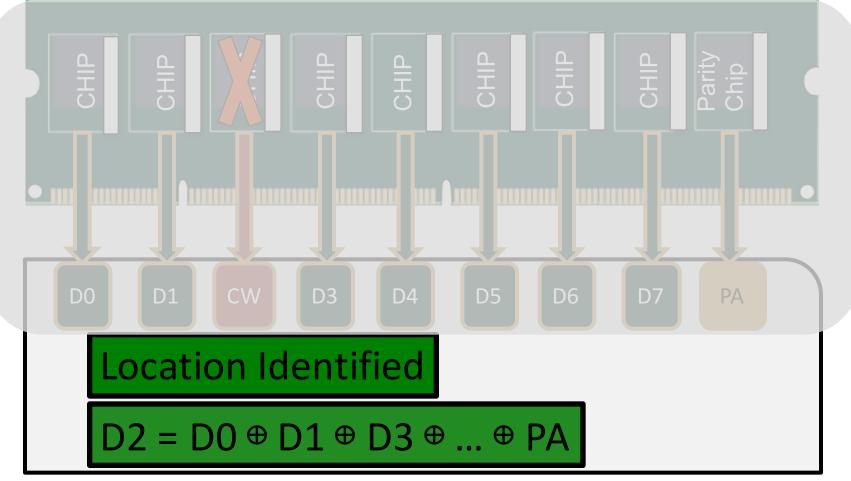
Catch Word (CW) ≠ Valid Data (D2)



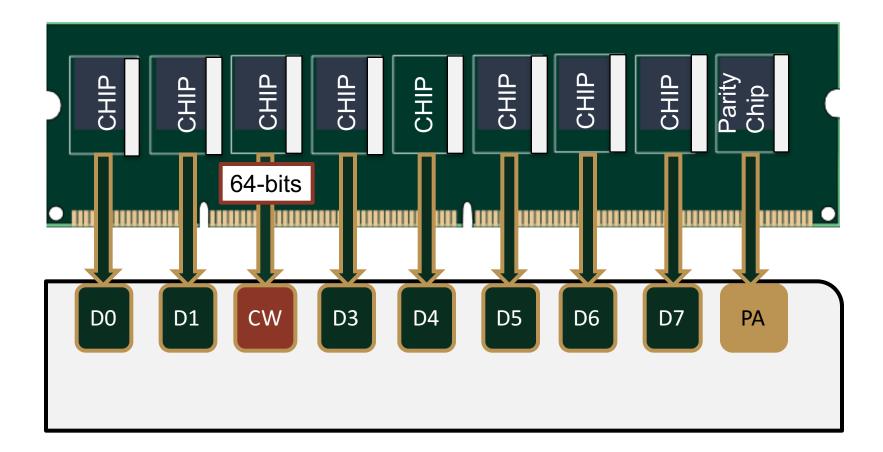
Catch Word (CW) \neq Valid Data (D2) Then \rightarrow PA \neq D0 \oplus D1 \oplus CW \oplus ... \oplus D7



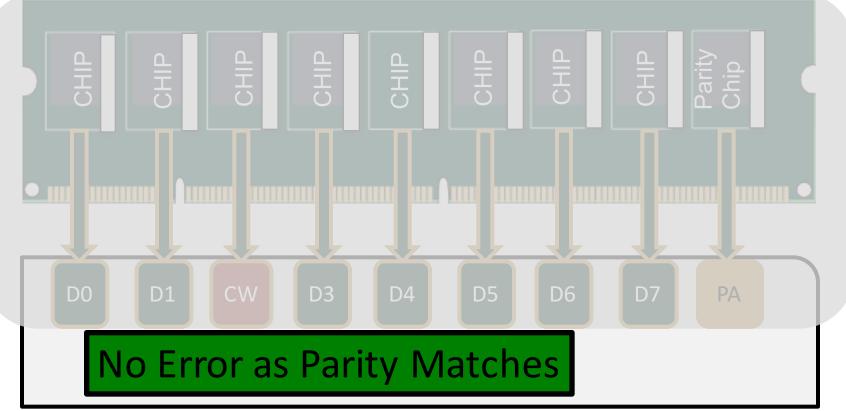
Catch Word (CW) \neq Valid Data (D2) Then \rightarrow PA \neq D0 \oplus D1 \oplus CW \oplus ... \oplus D7



Catch Word (CW) = Valid Data (D2)



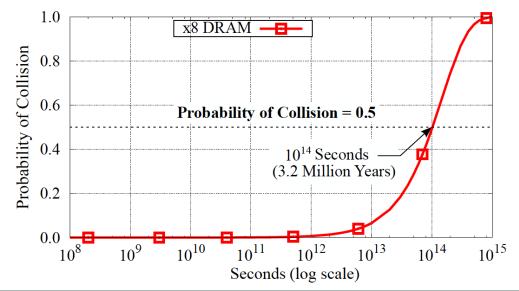
Catch Word (CW) = Valid Data (D2) [*Collision*] Then \rightarrow PA = D0 \oplus D1 \oplus CW \oplus ... \oplus D7



Catch-Word collision: Doesn't affect correctness

COLLISIONS: NOT A PROBLEM

- A chip stores 64 bits/cache-line \rightarrow 2⁶⁴ combinations
- However even a 16Gb chip has only 2²⁸ cachelines
- Even if this entire chip contained different data there are nearly 2^{63.99} data combinations free!



The catch-word will most likely not collide

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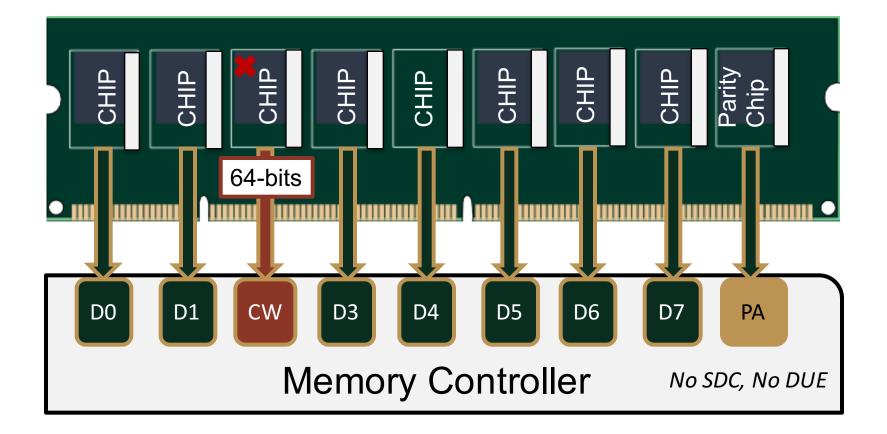
XED FOR SCALING ERRORS

On-Die ECC

- Single Error Correction
- Always detects scaling errors (single-bit)

CASE STUDY 1: SINGLE SCALING FAULT

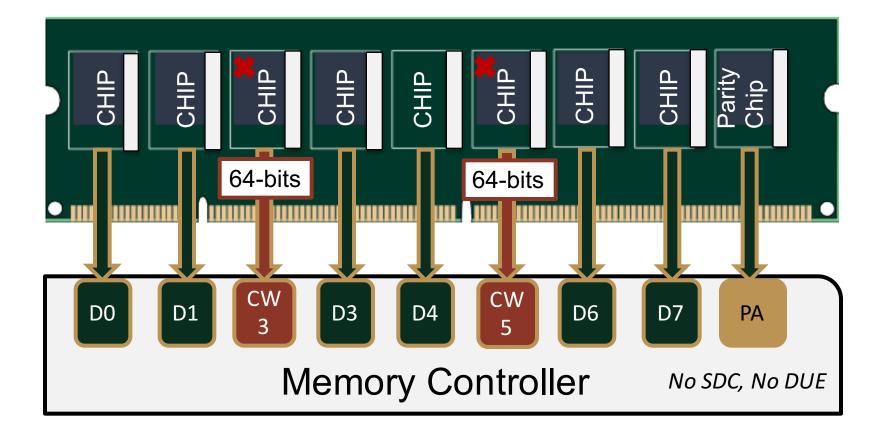
Scaling fault within a single chip



Parity reconstructs data from chip with scaling error

CASE STUDY 2: MULTIPLE SCALING FAULTS

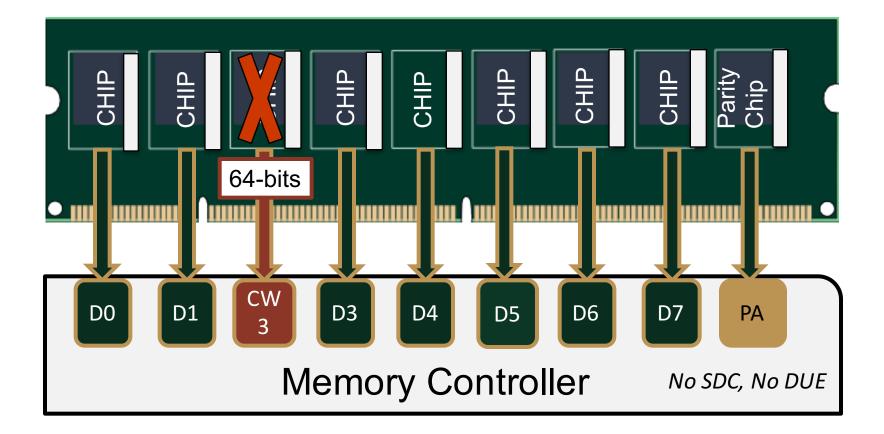
Scaling faults within multiple chips



Disable XED + Retry

CASE STUDY 3: CHIP FAULT

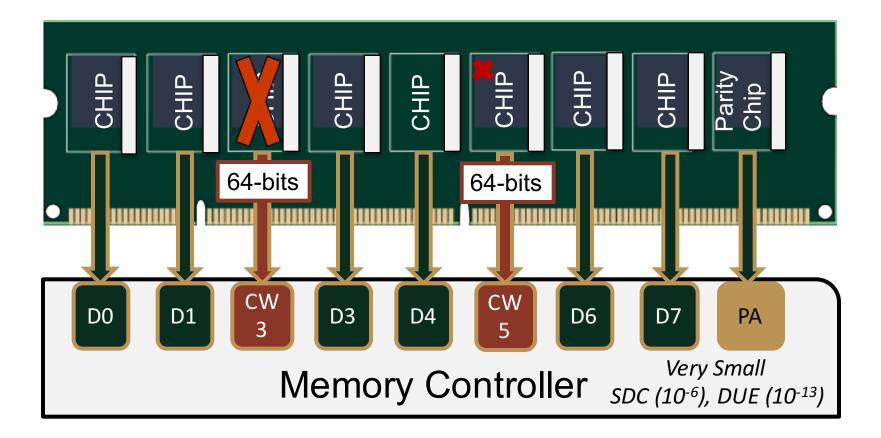
Catch-Word identifies the faulty chip



Parity reconstructs data from failed chip

CASE STUDY 4: CHIP + SCALING FAULT

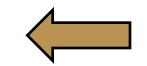
Parity detects error even after retry \rightarrow Chip Failure



Disable XED + Diagnosis to locate chip failure

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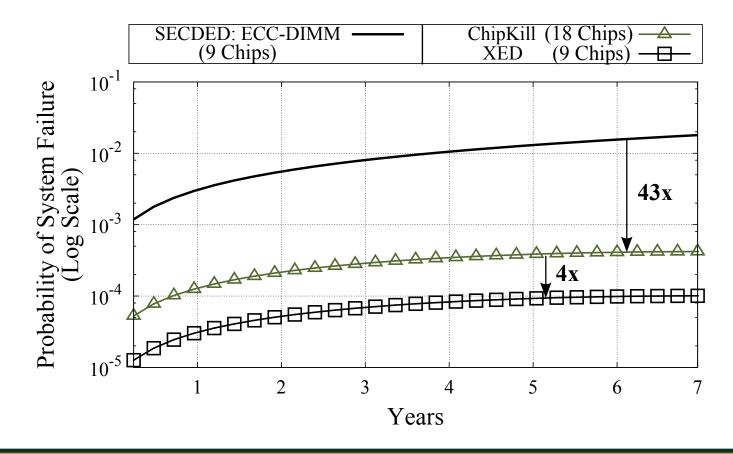
USIMM : 8 Cores, 4 Channels, 2 Ranks, 8 Banks

FaultSim*: Memory Reliability Simulator

- Real World Fault Data
- 7 year system lifetime,
- Billion Monte-Carlo Trails
- Metric: Probability of System Failure
- Scaling Fault-Rate: 10⁻⁴

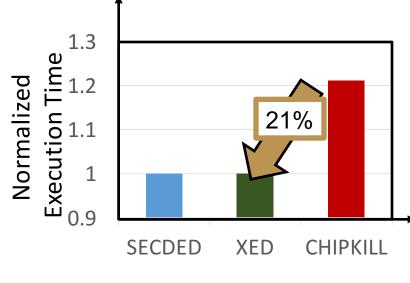
RESULTS: RELIABILITY

XED vs Commercial ECC schemes



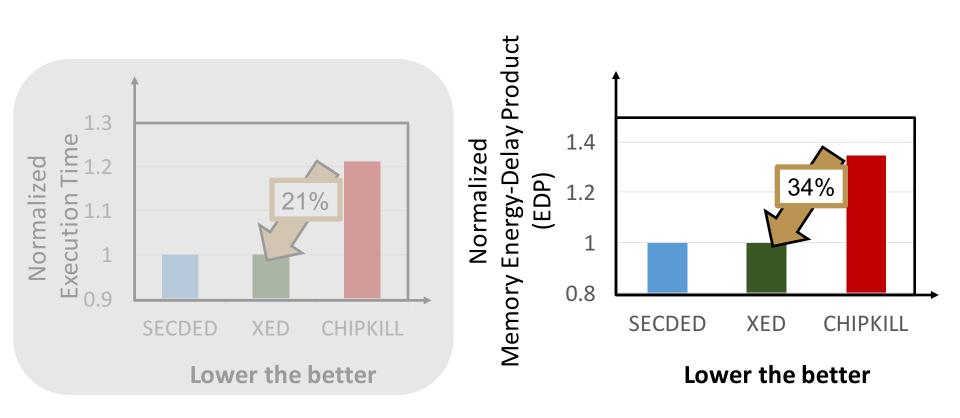
XED provides strong reliability while using fewer chips

RESULTS: PERFORMANCE AND EDP



Lower the better

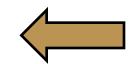
RESULTS: PERFORMANCE AND EDP



Execution time: 21% J, EDP : 34% J

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SUMMARY

- DRAM Scaling introduces errors \rightarrow On-Die ECC
- On-Die ECC is invisible to the memory system
- Exposing On-Die ECC: Efficient Runtime ECC
- XED
 - Exposes On-Die Error Detection using Catch-Words
 - 2X fewer chips as compared to Chipkill
 - 4X higher reliability as compared to Chipkill
 - 21% lower execution time as compared to Chipkill
- XED \rightarrow No change in memory protocols

THANK YOU



"You are in a pitiable condition, if you have to conceal what you wish to tell" - Publilius Syrus

BACKUP

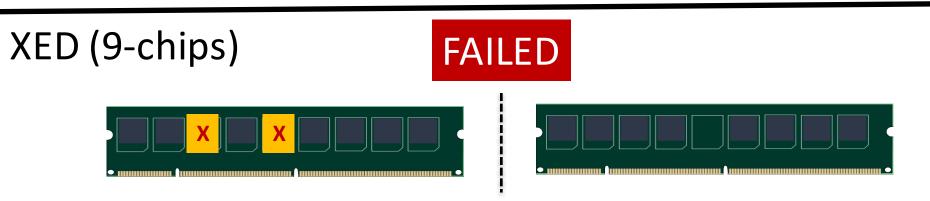
RANDOM DATA?

- What if only half the data is random
 - 1. Then average time for collision increases by 2x (3.2 Million Years \rightarrow 6.4 Million Years)
 - 2. Less random data increases collision time
- DIMMs today store scrambled (randomized) data
 - 1. To equalize the number of 1's and 0's
 - 2. Reduce Bit Error Rate on the bus
 - 3. Scrambling using address based hash

Lower randomization → Longer time till collision
Current systems anyway scramble data for fidelity

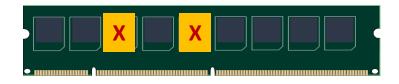
MTTF: XED VS CHIPKILL

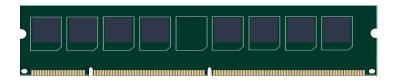
2-Chip Failures



Chipkill (18-chips)

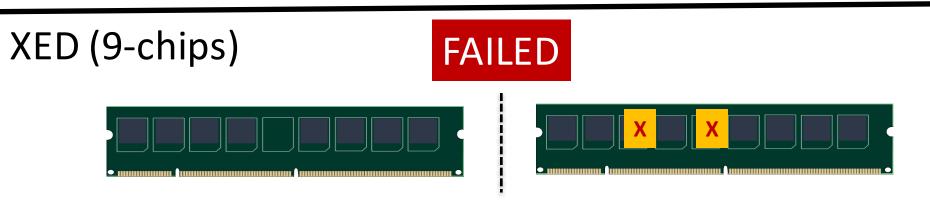






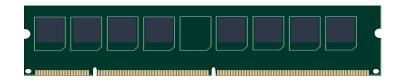
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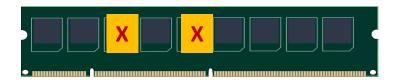
2-Chip Failures



Chipkill

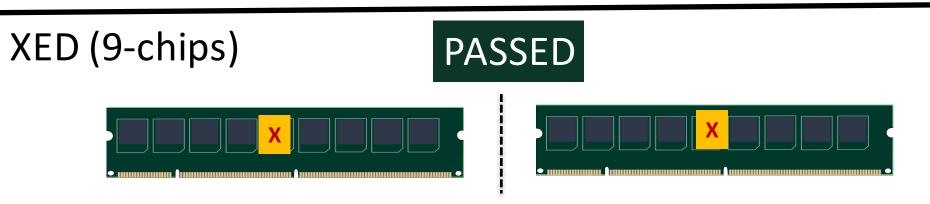






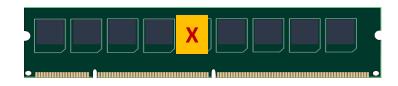
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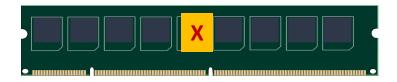
2-Chip Failures \rightarrow Extend to Multi-Chip Failures



Chipkill





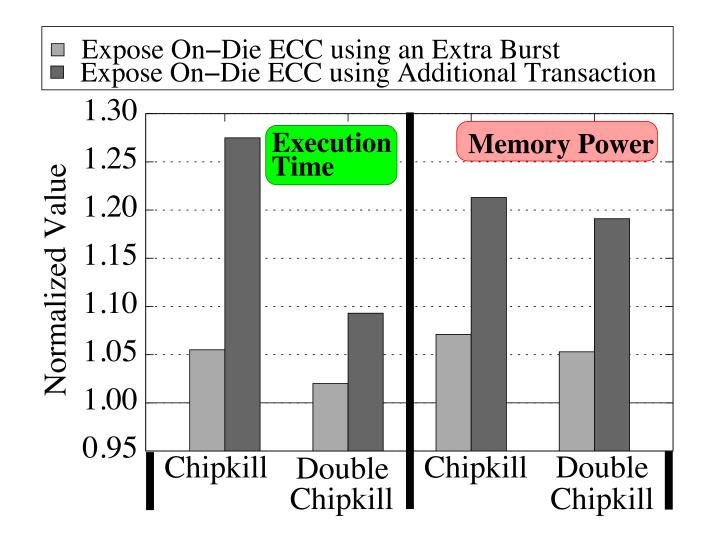


SDC AND DUE

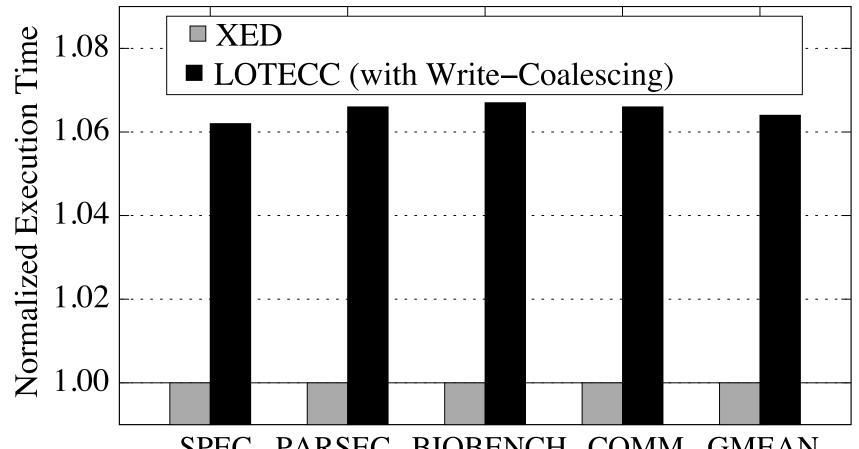
SDC AND DUE RATE OF XED

Source of Vulnerability	Rate over 7 years
XED: Scaling-Related Faults	No SDC or DUE
XED: Row/ Column/ Bank Failure	1.4×10^{-13} (SDC)
XED: Word Failure	6.1×10^{-6} (DUE)
Data Loss from Multi-Chip Failures	5.8×10^{-4}

ADDITIONAL BURST/TRANSACTION



XED VS LOT-ECC



SPEC PARSEC BIOBENCH COMM **GMEAN**